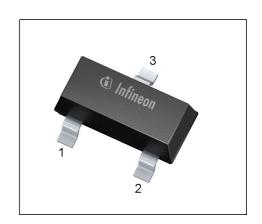


Low Noise Silicon Bipolar RF Transistor

- High linearity low noise RF transistor
- 22 dBm OP1dB and 31 dBm OIP3
 @ 900 MHz, 8 V, 70 mA
- For UHF / VHF applications
- Driver for multistage amplifiers
- For linear broadband and antenna amplifiers
- Collector design supports 5 V supply voltage
- Pb-free (RoHS compliant) package
- Qualification report according to AEC-Q101 available





ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pin Configuration			Package
BFR106	R7s	1=B	2=E	3=C	SOT23

Maximum Ratings at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-emitter voltage,	$V_{\sf CEO}$		V
$T_A = 25^{\circ}C$		16	
$T_{A} = -55^{\circ}C$		15	
Collector-emitter voltage	V _{CES}	20	
Collector-base voltage	V_{CBO}	20	
Emitter-base voltage	V _{EBO}	3	
Collector current	$I_{\mathbb{C}}$	210	mA
Base current	l _B	21	
Total power dissipation ¹⁾	P _{tot}	700	mW
<i>T</i> _S ≤ 76 °C			
Junction temperature	T_{J}	150	°C
Storage temperature	T_{Stq}	-55 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾	R _{thJS}	105	K/W

 $^{{}^{1}}T_{\rm S}$ is measured on the collector lead at the soldering point to the pcb

²For calculation of R_{thJS} please refer to Application Note AN077 (Thermal Resistance Calculation)



Electrical Characteristics at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Values		Unit	
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage	V _{(BR)CEO}	15	-	-	V
$I_{\rm C}$ = 1 mA, $I_{\rm B}$ = 0	, ,				
Collector-emitter cutoff current	I _{CES}				μΑ
$V_{CE} = 20 \text{ V}, V_{BE} = 0$		-	-	1	
$V_{CE} = 10 \text{ V}, V_{BE} = 0$		-	0.001	0.03	
Collector-base cutoff current	I _{CBO}	-	1	30	nA
$V_{CB} = 10 \text{ V}, I_{E} = 0$					
Emitter-base cutoff current	I _{EBO}	-	1	30	
$V_{\rm EB} = 2 \text{ V}, I_{\rm C} = 0$					
DC current gain	h _{FE}	70	100	140	-
$I_{\rm C}$ = 70 mA, $V_{\rm CE}$ = 8 V, pulse measured					



Electrical Characteristics at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit	
		min.	typ.	max.		
AC Characteristics (verified by random sampling)						
Transition frequency	f_{T}	3.5	5	-	GHz	
$I_{\rm C}$ = 70 mA, $V_{\rm CE}$ = 8 V, f = 500 MHz						
Collector-base capacitance	C _{cb}	-	0.85	1.2	pF	
$V_{\text{CB}} = 10 \text{ V}, f = 1 \text{ MHz}, V_{\text{BE}} = 0$,						
emitter grounded						
Collector emitter capacitance	C _{ce}	-	0.27	-		
$V_{CE} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0$,						
base grounded						
Emitter-base capacitance	C _{eb}	-	3.9	-		
$V_{\text{EB}} = 0.5 \text{ V}, f = 1 \text{ MHz}, V_{\text{CB}} = 0$,						
collector grounded						
Minimum noise figure	<i>NF</i> _{min}				dB	
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$,						
f = 900 MHz		-	1.8	-		
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$,						
f = 1.8 GHz		-	3	-		



Electrical Characteristics at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling	j)				
Power gain, maximum available ¹⁾	G _{ma}				dB
$I_{\rm C}$ = 70 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$, $Z_{\rm L}$ = $Z_{\rm Lopt}$,					
f = 900 MHz		-	13	-	
$I_{\rm C}$ = 70 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$, $Z_{\rm L}$ = $Z_{\rm Lopt}$,					
f = 1.8 GHz		-	8.5	-	
Transducer gain	$ S_{21e} ^2$				dB
$I_{\rm C}$ = 70 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω ,					
f = 900 MHz		-	10.5	-	
$I_{\rm C}$ = 70 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω ,					
f = 1.8 GHz		-	5	-	
Third order intercept point at output ²⁾	IP ₃	-	31	-	dBm
$V_{CE} = 8 \text{ V}, I_{C} = 70 \text{ mA}, f = 0.9 \text{ GHz},$					
$Z_{S}=Z_{L}=50\Omega$					
1dB compression point	P _{-1dB}	-	22	-	
$I_{\rm C}$ = 70 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ =50 Ω ,					
f = 0.9 GHz					

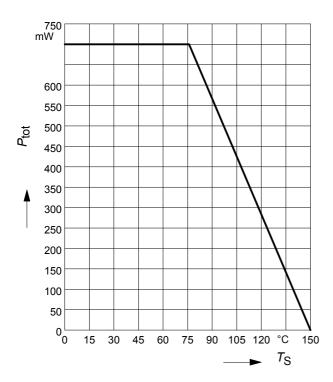
 $^{{}^{1}}G_{\text{ma}} = |S_{21e} / S_{12e}| (k-(k^{2}-1)^{1/2})$

 $^{{}^2\}emph{IP}_3$ value depends on termination of all intermodulation frequency components.

Termination used for this measurement is 50Ω from 0.1 MHz to 6 GHz



Total power dissipation $P_{\text{tot}} = f(T_{\text{S}})$





SPICE GP Model

For the SPICE Gummel Poon (GP) model as well as for the S-parameters (including noise parameters) please refer to our internet website www.infineon.com/rf.models.

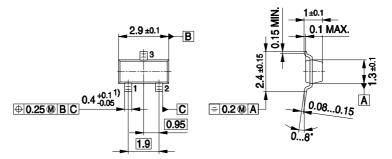
Please consult our website and download the latest versions before actually starting your design.

6



Package Outline

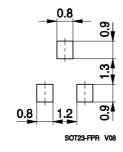




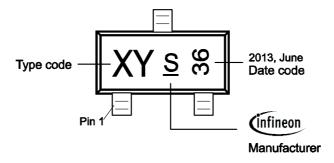
1) Lead width can be 0.6 max. in dambar area

SOT23-PO V08

Foot Print

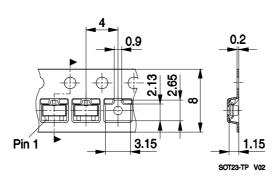


Marking Layout



Standard Packing

Reel o 180 mm: 3.000 Pieces / Reel Reel o 330 mm = 10.000 Pieces / Reel





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